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SIDDHARTH INSTITUTE OF ENGINEERING & TECHNOLOGY:: PUTTUR
(AUTONOMOUS)**M.Tech I Year I Semester (R16) Regular & Supplementary Examinations February 2018**
VLSI TECHNOLOGY

(Common to ES & VLSI)

Time: 3 hours

Max. Marks: 60

(Answer all Five Units 5 X 12 =60 Marks)

UNIT-I

- 1 a. Explain different steps involved in preparation CMOS using twin tub process. 7M
b. Derive the expression for ZPU/ZPD. 5M

OR

- 2 a. Explain a Bi-CMOS inverter with appropriate circuit. 6M
b. Explain effect of latch-up in CMOS circuits. 6M

UNIT-II

- 3 a. Explain switch Logic and Alternative Logic. 7M
b. Explain clearly the Scalable design rules. 5M

OR

- 4 a. Explain how stick diagrams can be used for layout diagrams. 7M
b. Discuss about the effects of scaling down the dimensions of MOS circuits and Systems. 5M

UNIT-III

- 5 a. Draw the layout diagram of three input NAND gate in CMOS. 6M
b. With suitable examples explain about network delays combinational logic circuits. 6M

OR

- 6 a. Explain the clocking disciplines and power optimization in sequential systems. 7M
b. Explain the structure of LSSD with suitable diagram. 5M

UNIT-IV

- 7 Explain floor planning methods of chip. 12 M

OR

- 8 a. Explain power reduction using Architecture driven voltage scaling method. 7M
b. Draw and explain the I/O architecture. 5M

UNIT-V

- 9 a. With an example give the method involved in the chip design. 7M
b. Write about test generation pattern. 5M

OR

- 10 a. Write about switch level simulation. 7M
b. Write short notes on sequential machine optimizations. 5M

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